

DIGITAL AMPLIFIER POWER STAGE



FEATURES

- 50 W per Channel (BTL) Into 6 Ω (Stereo)
- 95-dB Dynamic Range With TAS5026
- Less Than 0.1% THD+N (1 W RMS Into 6 Ω)
- Less Than 0.2% THD+N (50 W RMS into 6 Ω)
- Power Efficiency Typically 90% Into 6- Ω Load
- Self-Protecting Design (Undervoltage, Overtemperature and Short Conditions) With Error Reporting
- Internal Gate Drive Supply Voltage Regulator
- EMI Compliant When Used With Recommended System Design

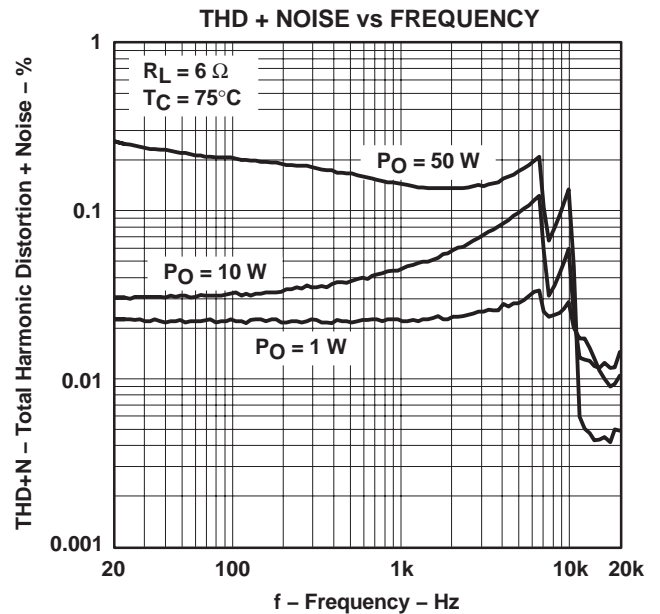
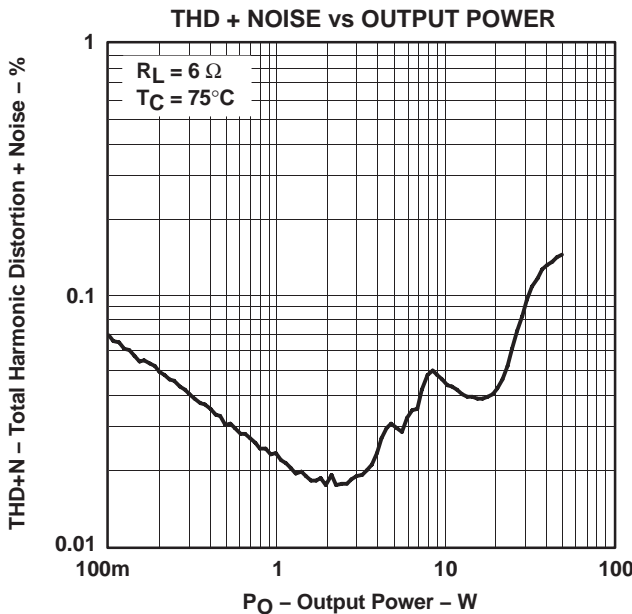
APPLICATIONS

- DVD Receiver
- Home Theatre
- Mini/Micro Component Systems
- Internet Music Appliance

DESCRIPTION

The TAS5112 is a high-performance, integrated stereo digital amplifier power stage designed to drive 6- Ω speakers at up to 50 W per channel. The device incorporates TI's PurePath Digital™ technology and is used with a digital audio PWM processor (TAS50XX) and a simple passive demodulation filter to deliver high-quality, high-efficiency, true-digital audio amplification.

The efficiency of this digital amplifier is typically 90%, reducing the size of both the power supplies and heatsinks needed. Overcurrent protection, overtemperature protection, and undervoltage protection are built into the TAS5112, safeguarding the device and speakers against fault conditions that could damage the system.



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TAS5112

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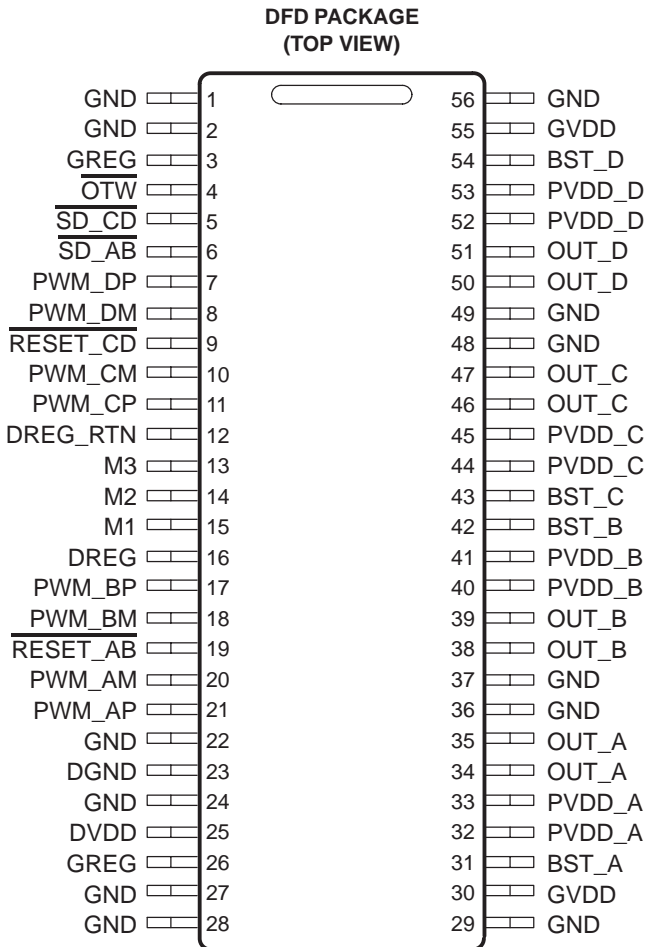


These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

GENERAL INFORMATION

Terminal Assignment

The TAS5112 is offered in a thermally enhanced 56-pin TSSOP DFD (thermal pad is on the top), shown as follows.



ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted⁽¹⁾

| TAS5112 | UNITS |
|--|------------------------|
| DVDD TO DGND | -0.3 V to 4.2 V |
| GVDD TO GND | 33.5 V |
| PVDD_X TO GND (dc voltage) | 33.5 V |
| PVDD_X TO GND (spike voltage ⁽²⁾) | 48 V |
| OUT_X TO GND (dc voltage) | 33.5 V |
| OUT_X TO GND (spike voltage ⁽²⁾) | 48 V |
| BST_X TO GND (dc voltage) | 48 V |
| BST_X TO GND (spike voltage ⁽²⁾) | 53 V |
| GREG TO GND ⁽³⁾ | 14.2 V |
| PWM_XP, RESET, M1, M2, M3, SD, OTW | -0.3 V to DVDD + 0.3 V |
| Maximum operating junction temperature, T _J | -40°C to 150°C |
| Storage temperature | -40°C to 125°C |

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

⁽²⁾ The duration of voltage spike should be less than 100 ns.

⁽³⁾ GREG is treated as an input when the GREG pin is overdriven by GVDD of 12 V.

ORDERING INFORMATION

| T _A | PACKAGE | DESCRIPTION |
|----------------|------------|--------------------|
| 0°C to 70°C | TAS5112DFD | 56-pin small TSSOP |

⁽¹⁾ For the most current specification and package information, refer to our Web site at www.ti.com.

PACKAGE DISSIPATION RATINGS

| PACKAGE | R _{θJC} (°C/W) | R _{θJA} (°C/W) |
|------------------|-------------------------|-------------------------|
| 56-pin DAD TSSOP | 1.14 | See Note 1 |

⁽¹⁾ The TAS5112 package is thermally enhanced for conductive cooling using an exposed metal pad area. It is impractical to use the device with the pad exposed to ambient air as the only heat sinking of the device.

For this reason, R_{θJA}, a system parameter that characterizes the thermal treatment, is provided in the *Application Information* section of the data sheet. An example and discussion of typical system R_{θJA} values are provided in the *Thermal Information* section. This example provides additional information regarding the power dissipation ratings. This example should be used as a reference to calculate the heat dissipation ratings for a specific application. TI application engineering provides technical support to design heatsinks if needed.

Terminal Functions

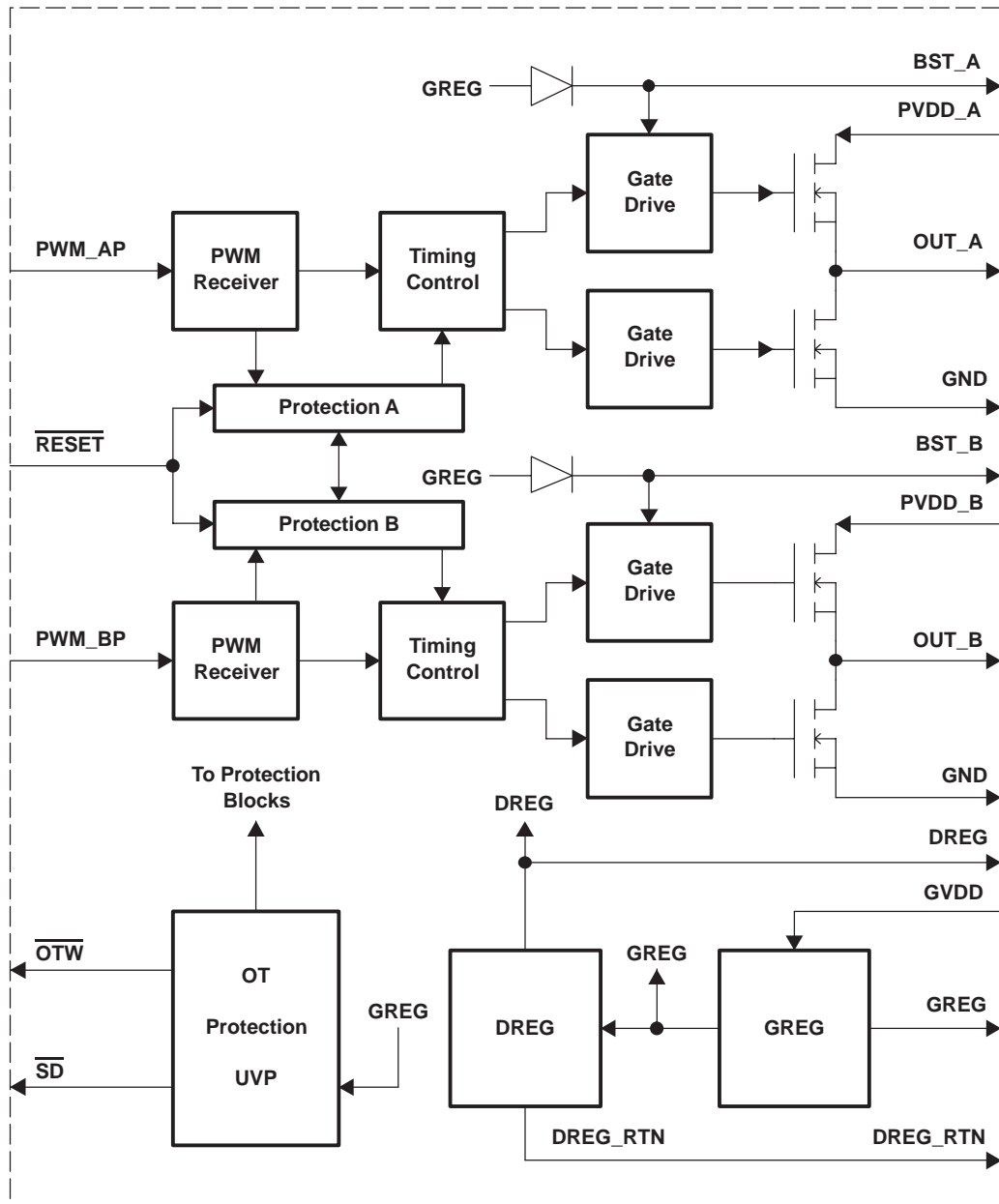
| TERMINAL | | FUNCTION ⁽¹⁾ | DESCRIPTION |
|-----------|--|-------------------------|---|
| NAME | NO. | | |
| BST_A | 31 | P | High-side bootstrap supply (BST), external capacitor to OUT_A required |
| BST_B | 42 | P | High-side bootstrap supply (BST), external capacitor to OUT_B required |
| BST_C | 43 | P | HS bootstrap supply (BST), external capacitor to OUT_C required |
| BST_D | 54 | P | HS bootstrap supply (BST), external capacitor to OUT_D required |
| DGND | 23 | P | Digital I/O reference ground |
| DREG | 16 | P | Digital supply voltage regulator decoupling pin, capacitor connected to GND |
| DREG_RTN | 12 | P | Digital supply voltage regulator decoupling return pin |
| DVDD | 25 | P | I/O reference supply input (3.3 V) |
| GND | 1, 2, 22, 24, 27, 28, 29, 36, 37, 48, 49, 56 | P | Power ground |
| GREG | 3, 26 | P | Gate drive voltage regulator decoupling pin, capacitor to REG_GND |
| GVDD | 30, 55 | P | Voltage supply to on-chip gate drive and digital supply voltage regulators |
| M1 (TST0) | 15 | I | Mode selection pin |
| M2 | 14 | I | Mode selection pin |
| M3 | 13 | I | Mode selection pin |
| OTW | 4 | O | Overtemperature warning output, open drain with internal pullup resistor |
| OUT_A | 34, 35 | O | Output, half-bridge A |
| OUT_B | 38, 39 | O | Output, half-bridge B |
| OUT_C | 46, 47 | O | Output, half-bridge C |
| OUT_D | 50, 51 | O | Output, half-bridge D |
| PVDD_A | 32, 33 | P | Power supply input for half-bridge A |
| PVDD_B | 40, 41 | P | Power supply input for half-bridge B |
| PVDD_C | 44, 45 | P | Power supply input for half-bridge C |
| PVDD_D | 52, 53 | P | Power supply input for half-bridge D |
| PWM_AM | 20 | I | Input signal (negative), half-bridge A |
| PWM_AP | 21 | I | Input signal (positive), half-bridge A |
| PWM_BM | 18 | I | Input signal (negative), half-bridge B |
| PWM_BP | 17 | I | Input signal (positive), half-bridge B |
| PWM_CM | 10 | I | Input signal (negative), half-bridge C |
| PWM_CP | 11 | I | Input signal (positive), half-bridge C |
| PWM_DM | 8 | I | Input signal (negative), half-bridge D |
| PWM_DP | 7 | I | Input signal (positive), half-bridge D |
| RESET_AB | 19 | I | Reset signal, active low |
| RESET_CD | 9 | I | Reset signal, active low |
| SD_AB | 6 | O | Shutdown signal for half-bridges A and B, active-low |
| SD_CD | 5 | O | Shutdown signal for half-bridges C and D, active-low |

⁽¹⁾ I = input, O = Output, P = Power

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FUNCTIONAL BLOCK DIAGRAM



This diagram shows one channel.

RECOMMENDED OPERATING CONDITIONS

| | | | MIN | TYP | MAX | UNIT |
|----------------|---|--|-----|------|------|------|
| DVDD | Digital supply ⁽¹⁾ | Relative to DGND | 3 | 3.3 | 3.6 | V |
| GVDD | Supply for internal gate drive and logic regulators | Relative to GND | 16 | 29.5 | 30.5 | V |
| PVDD_x | Half-bridge supply | Relative to GND, R _L = 6 Ω to 8 Ω | 0 | 29.5 | 30.5 | V |
| T _J | Junction temperature | | 0 | | 125 | °C |

(1) It is recommended for DVDD to be connected to DREG via a 100-Ω resistor.

ELECTRICAL CHARACTERISTICS

PVDD_X = 29.5 V, GVDD = 29.5 V, DVDD connected to DREG via a 100-Ω resistor, R_L = 6 Ω, 8X f_S = 384 kHz, unless otherwise noted

| SYMBOL | PARAMETER | TEST CONDITIONS | TYPICAL | OVER TEMPERATURE | | | | |
|--|-----------------------------------|---|----------------------|----------------------|-------------------------|------------------------------|-------|--------------|
| | | | T _A =25°C | T _A =25°C | T _{Case} =75°C | T _A =40°C TO 85°C | UNITS | MIN/TYP/ MAX |
| AC PERFORMANCE, BTL Mode, 1 kHz | | | | | | | | |
| P _o | Output power | R _L = 8 Ω, THD = 0.2%, AES17 filter, 1 kHz | | | 40 | | W | Typ |
| | | R _L = 8 Ω, THD = 10%, AES17 filter, 1 kHz | | | 50 | | W | Typ |
| | | R _L = 6 Ω, THD = 0.2%, AES17 filter, 1 kHz | | | 50 | | W | Typ |
| | | R _L = 6 Ω, THD = 10%, AES17 filter, 1 kHz | | | 62 | | W | Typ |
| THD+N | Total harmonic distortion + noise | P _o = 1 W/ channel, R _L = 6 Ω, AES17 filter | | | 0.03% | | | Typ |
| | | P _o = 10 W/channel, R _L = 6 Ω, AES17 filter | | | 0.04% | | | Typ |
| | | P _o = 50 W/channel, R _L = 6 Ω, AES17 filter | | | 0.2% | | | Typ |
| V _n | Output integrated voltage noise | A-weighted, mute, R _L = 6 Ω, 20 Hz to 20 kHz, AES17 filter | | | 260 | | μV | Max |
| SNR | Signal-to-noise ratio | A-weighted, AES17 filter | | | 96 | | dB | Typ |
| DR | Dynamic range | f = 1 kHz, A-weighted, AES17 filter | | | 96 | | dB | Typ |
| INTERNAL VOLTAGE REGULATOR | | | | | | | | |
| DREG | Voltage regulator | I _o = 1 mA, PVDD = 18 V–30.5 V | 3.1 | | | | V | Typ |
| GREG | Voltage regulator | I _o = 1.2 mA, PVDD = 18 V–30.5 V | 13.4 | | | | V | Typ |
| IVGDD | GVDD supply current, operating | f _S = 384 kHz, no load, 50% duty cycle | | 24 | | | mA | Max |
| IDVDD | DVDD supply current, operating | f _S = 384 kHz, no load | 1 | 5 | | | mA | Max |
| OUTPUT STAGE MOSFETS | | | | | | | | |
| R _{on,LS} | Forward on-resistance, low side | T _J = 25°C | 155 | | | | mΩ | Typ |
| R _{on,HS} | Forward on-resistance, high side | T _J = 25°C | 155 | | | | mΩ | Typ |

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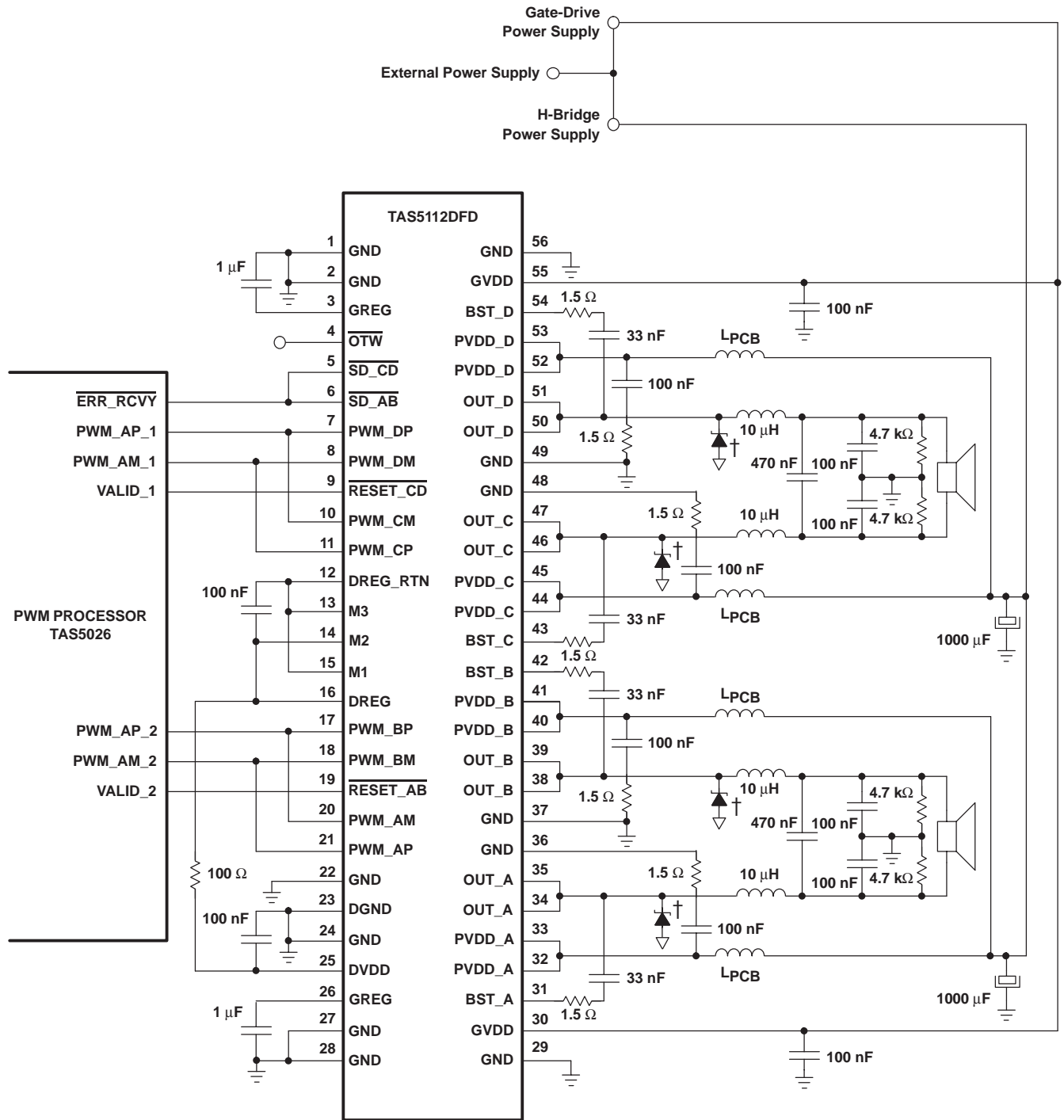
ELECTRICAL CHARACTERISTICS

 PVDD_x = 29.5 V, GVDD = 29.5 V, DVDD connected to DREG via a 100-Ω resistor, R_L = 6 Ω, 8X f_S = 384 kHz, unless otherwise noted

| SYMBOL | PARAMETER | TEST CONDITIONS | TYPICAL | OVER TEMPERATURE | | | | |
|-------------------------------------|--|---|----------------------|----------------------|-------------------------|------------------------------|-------|-------------|
| | | | T _A =25°C | T _A =25°C | T _{Case} =75°C | T _A =40°C TO 85°C | UNITS | MIN/TYP/MAX |
| INPUT/OUTPUT PROTECTION | | | | | | | | |
| V _{uvp,G} | Undervoltage protection limit, GVDD | Set the DUT in normal operation mode with all the protections enabled. Sweep GVDD up and down. Monitor \overline{SD} output. Record the GREG reading when \overline{SD} is triggered. | 7.4 | 6.9 | | | V | Min |
| | | | | 7.9 | | | V | Max |
| OTW | Overtemperature warning, junction temperature | | 125 | | | | °C | Typ |
| OTE | Overtemperature error, junction temperature | | 150 | | | | °C | Typ |
| OC | Overcurrent protection | See Note 1. | 5.8 | | | | A | Typ |
| STATIC DIGITAL SPECIFICATION | | | | | | | | |
| | PWM_AP, PWM_BP, M1, M2, M3, \overline{SD} , \overline{OTW} | | | | | | | |
| V _{IH} | High-level input voltage | | | 2 | | | V | Min |
| | | | | DVDD | | | V | Max |
| V _{IL} | Low-level input voltage | | | 0.8 | | | V | Max |
| Leakage | Input leakage current | | | -10 | | | μA | Min |
| | | | | 10 | | | μA | Max |
| OTW/SHUTDOWN (SD) | | | | | | | | |
| | Internally pull up R from $\overline{OTW/SD}$ to DVDD | | 30 | 22.5 | | | kΩ | Min |
| V _{OL} | Low-level output voltage | I _O = 4 mA | | 0.4 | | | V | Max |

(1) To optimize device performance and prevent overcurrent (OC) protection tripping, the demodulation filter must be designed with special care. See *Demodulation Filter Design* in the *Application Information* section of the data sheet and consider the recommended inductors and capacitors for optimal performance. It is also important to consider PCB design and layout for optimum performance of the TAS5112. It is recommended to follow the TAS5112F2EVM (S/N 112) design and layout guidelines for best performance.

SYSTEM CONFIGURATION USED FOR CHARACTERIZATION



L_{PCB} : TRACK IN THE PCB (1,0 mm wide and 50 mm long)

† Voltage Suppressor Diode: 1SMA33CAT

TYPICAL CHARACTERISTICS AND SYSTEM PERFORMANCE
OF TAS5112 EVM WITH TAS5026 PWM PROCESSOR

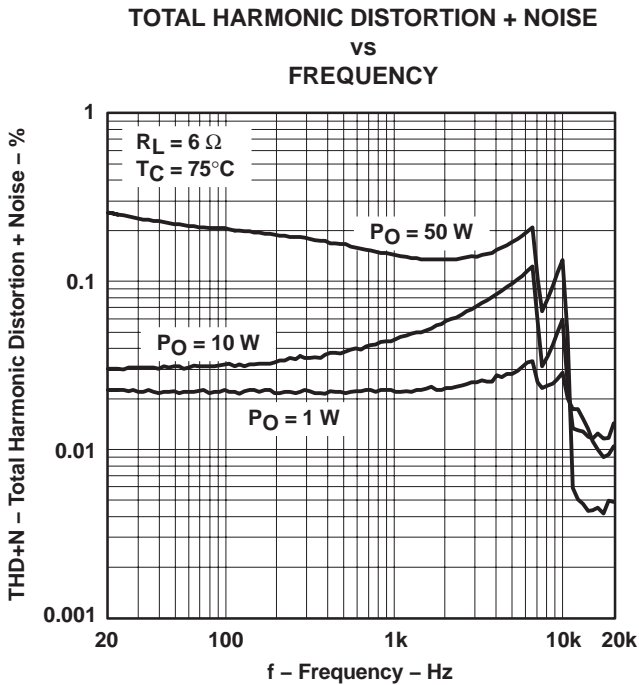


Figure 1

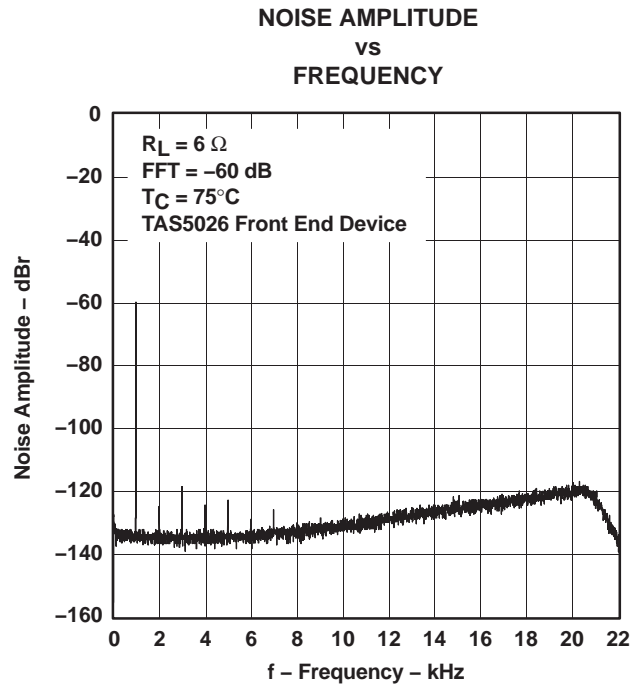


Figure 2

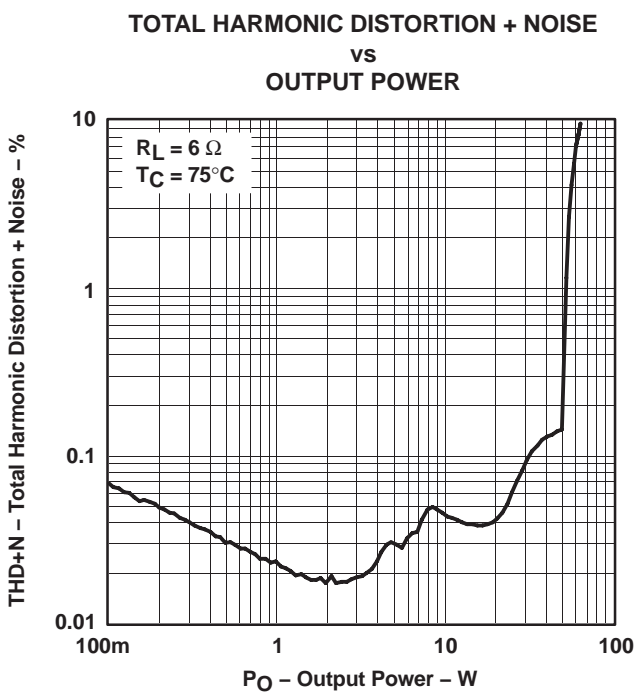


Figure 3

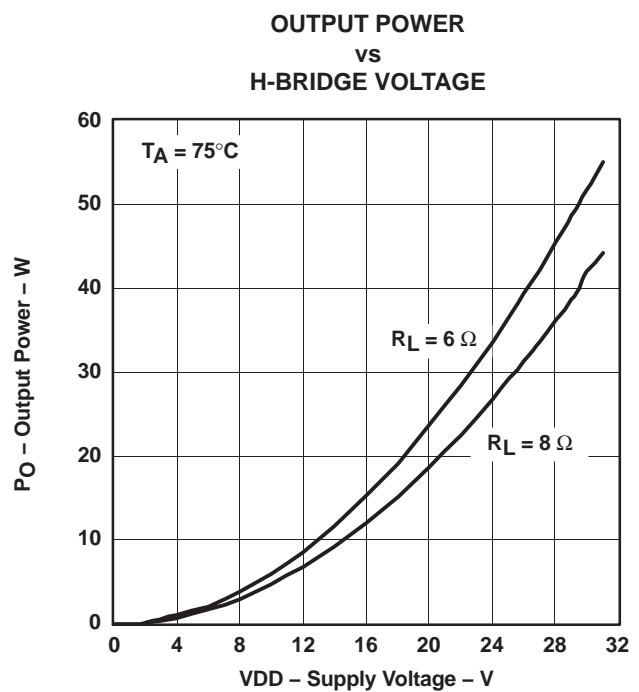


Figure 4

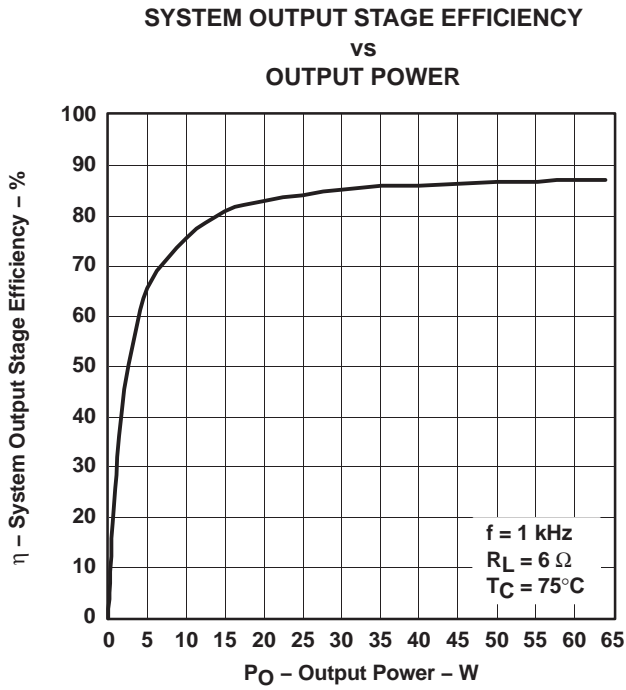


Figure 5

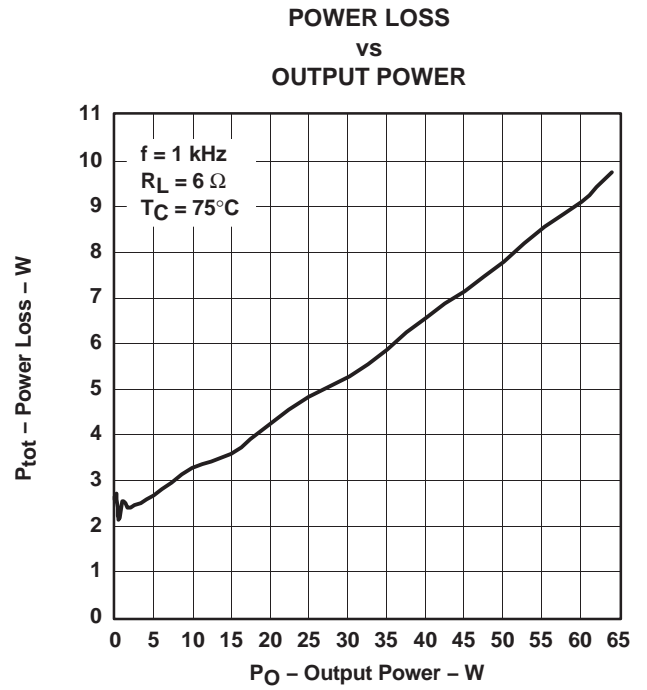


Figure 6

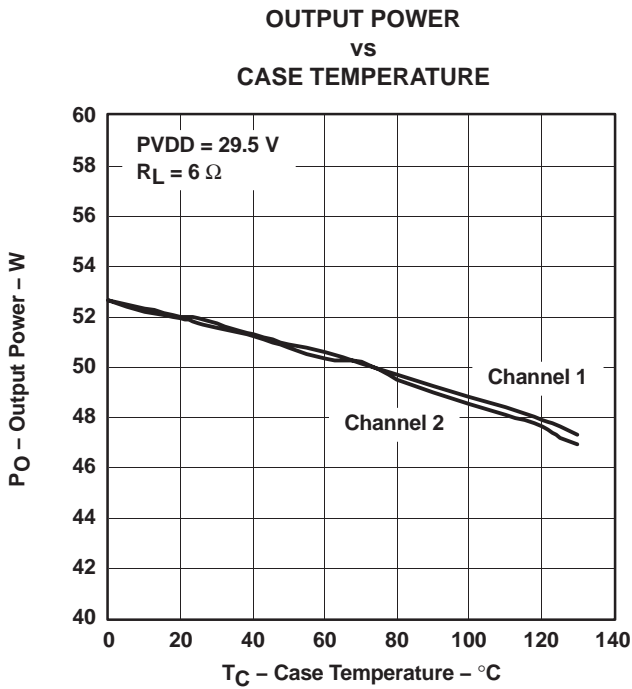


Figure 7

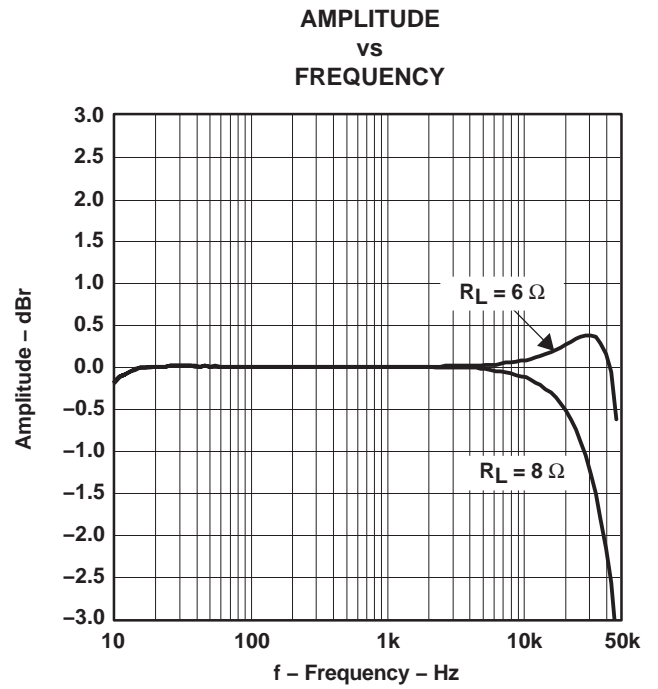


Figure 8

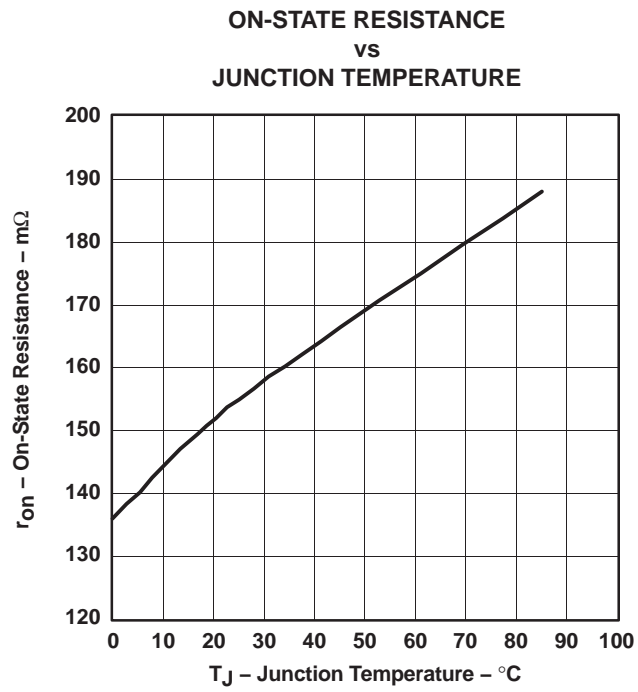


Figure 9

THEORY OF OPERATION

POWER SUPPLIES

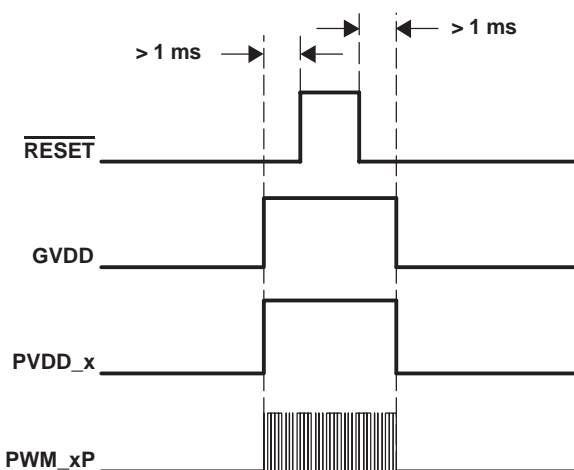
The power device only requires two supply voltages, GVDD and PVDD_X.

GVDD is the gate drive supply for the device, regulated internally down to approximately 12 V, and decoupled with regards to board GND on the GREG pins through an external capacitor. GREG powers both the low side and high side via a bootstrap step-up conversion. The bootstrap supply is charged after the first low-side turn-on pulse. Internal digital core voltage DREG is also derived from GVDD and regulated down by internal circuitry to 3.3 V.

The gate-driver regulator can be bypassed for reducing idle loss in the device by shorting GREG to GVDD and directly feeding in 12.0 V. This can be useful in an application where thermal conduction of heat from the device is difficult.

PVDD_X is the H-bridge power supply pin. Two power pins exist for each half-bridge to handle the current density. It is important that the circuitry recommendations around the PVDD_X pins are followed carefully both topology- and layout-wise. For topology recommendations, see the *Typical System Configuration* section. Following these recommendations is important for parameters like EMI, reliability, and performance.

POWERING UP



NOTE: PVDD should not be powered up before GVDD.

During power up when $\overline{\text{RESET}}$ is asserted LOW, all MOSFETs are turned off and the two internal half-bridges are in the high-impedance state (Hi-Z). The bootstrap capacitors supplying high-side gate drive are not charged at this point. To comply with the click and pop scheme and use of non-TI modulators it is recommended to use a 4-k Ω pulldown resistor on each PWM output node to ground.

This precharges the bootstrap supply capacitors and discharges the output filter capacitor (see the *Typical TAS5112 Application Configuration* section).

After GVDD has been applied, it takes approximately 800 μs to fully charge the BST capacitor. Within this time, $\overline{\text{RESET}}$ must be kept low. After approximately 1 ms, the back-end bootstrap capacitor is charged.

$\overline{\text{RESET}}$ can now be released if the modulator is powered up and streaming valid PWM signals to the back-end PWM_xP. Valid means a switching PWM signal which complies with the frequency and duty cycle ranges stated in the *Recommended Operating Conditions*.

A constant HIGH dc level on the PWM_xP is not permitted, because it would force the high-side MOSFET ON until it eventually ran out of BST capacitor energy and might damage the device.

An unknown state of the PWM output signals from the modulator is illegal and should be avoided, which in practice means that the PWM processor must be powered up and initialized before $\overline{\text{RESET}}$ is de-asserted HIGH to the back end.

POWERING DOWN

For power down of the back end, an opposite approach is necessary. The $\overline{\text{RESET}}$ must be asserted LOW before the valid PWM signal is removed.

When PWM processors are used with TI PurePath Digital amplifiers, the correct timing control of $\overline{\text{RESET}}$ and PWM_xP is performed by the modulator.

PRECAUTION

The TAS5112 must always start up in the high-impedance (Hi-Z) state. In this state, the bootstrap (BST) capacitor is precharged by a resistor on each PWM output node to ground. See the system configuration. This ensures that the back end is ready for receiving PWM pulses, indicating either HIGH- or LOW-side turnon after $\overline{\text{RESET}}$ is de-asserted to the back end.

With the following pulldown resistor and BST capacitor size, the charge time is:

$$C = 33 \text{ nF}, R = 4.7 \text{ k}\Omega$$

$$R \times C \times 5 = 775.5 \mu\text{s}$$

After GVDD has been applied, it takes approximately 800 μs to fully charge the BST capacitor. During this time, $\overline{\text{RESET}}$ must be kept low. After approximately 1 ms the back end BST is charged and ready. $\overline{\text{RESET}}$ can now be released if the PWM modulator is ready and is streaming valid PWM signals to the back end. Valid PWM signals are switching PWM signals with a frequency between 350–400 kHz. A constant HIGH level on the PWM+ would force the high-side MOSFET ON until it eventually ran out of BST capacitor energy. Putting the device in this condition should be avoided.

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In practice this means that the DVDD-to-PWM processor (front-end) should be stable and initialization should be completed before $\overline{\text{RESET}}$ is de-asserted to the back end.

CONTROL I/O

Shutdown Pin: $\overline{\text{SD}}$

The $\overline{\text{SD}}$ pin functions as an output pin and is intended for protection-mode signaling to, for example, a controller or other front-end device. The pin is open-drain with an internal pullup resistor to DVDD.

The logic output is, as shown in the following table, a combination of the device state and $\overline{\text{RESET}}$ input:

| $\overline{\text{SD}}$ | $\overline{\text{RESET}}$ | DESCRIPTION |
|------------------------|---------------------------|--|
| 0 | 0 | Not used |
| 0 | 1 | Device in protection mode, i.e., UVP and/or OC and/or OT error |
| 1(1) | 0 | Device set high-impedance (Hi-Z), $\overline{\text{SD}}$ forced high |
| 1 | 1 | Normal operation |

(1) $\overline{\text{SD}}$ is pulled high when $\overline{\text{RESET}}$ is asserted low independent of chip state (i.e., protection mode). This is desirable to maintain compatibility with some TI PWM front ends.

Temperature Warning Pin: $\overline{\text{OTW}}$

The $\overline{\text{OTW}}$ pin gives a temperature warning signal when temperature exceeds the set limit. The pin is of the open-drain type with an internal pullup resistor to DVDD.

| $\overline{\text{OTW}}$ | DESCRIPTION |
|-------------------------|--|
| 0 | Junction temperature higher than 125°C |
| 1 | Junction temperature lower than 125°C |

Overall Reporting

The $\overline{\text{SD}}$ pin, together with the $\overline{\text{OTW}}$ pin, gives chip state information as described in Table 1.

Table 1. Error Signal Decoding

| $\overline{\text{OTW}}$ | $\overline{\text{SD}}$ | DESCRIPTION |
|-------------------------|------------------------|--|
| 0 | 0 | Overtemperature error (OTE) |
| 0 | 1 | Overtemperature warning (OTW) |
| 1 | 0 | Overcurrent (OC) or undervoltage (UVP) error |
| 1 | 1 | Normal operation, no errors/warnings |

Chip Protection

The TAS5112 protection function is implemented in a closed loop with, for example, a system controller and TI PWM processor. The TAS5112 contains three individual systems protecting the device against error conditions. All of the error events covered result in the output stage being set in a high-impedance state (Hi-Z) for maximum protection of the device and connected equipment.

The device can be recovered by toggling $\overline{\text{RESET}}$ low and then high, after all errors are cleared.

Overcurrent (OC) Protection

The device has individual forward current protection on both high-side and low-side power stage FETs. The OC protection works only with the demodulation filter present at the output. See *Demodulation Filter Design* in the *Application Information* section of the data sheet for design constraints.

Overtemperature (OT) Protection

A dual temperature protection system asserts a warning signal when the device junction temperature exceeds 125°C. The OT protection circuit is shared by all half-bridges.

Undervoltage (UV) Protection

Undervoltage lockout occurs when GVDD is insufficient for proper device operation. The UV protection system protects the device under power-up and power-down situations. The UV protection circuits are shared by all half-bridges.

Reset Function

The function of the reset input is twofold:

- Reset is used for re-enabling operation after a latching error event.
- Reset is used for disabling output stage switching (mute function).

The error latch is cleared on the falling edge of reset and normal operation is resumed when reset goes high.

PROTECTION MODE

Autorecovery (AR) After Errors (PMODE0)

In autorecovery mode (PMODE0) the TAS5112 is self-supported in handling of error situations. All protection systems are active, setting the output stage in the high-impedance state to protect the output stage and connected equipment. However, after a short time the device autorecovers, i.e., operation is automatically resumed provided that the system is fully operational.

The autorecovery timing is set by counting PWM input cycles, i.e., the timing is relative to the switching frequency.

The AR system is common to both half-bridges.

Timing and Function

The function of the autorecovery circuit is as follows:

1. An error event occurs and sets the protection latch (output stage goes Hi-Z).
2. The counter is started.
3. After $n/2$ cycles, the protection latch is cleared but the output stage remains Hi-Z (identical to pulling $\overline{\text{RESET}}$ low).
4. After n cycles, operation is resumed (identical to pulling $\overline{\text{RESET}}$ high) ($n = 512$).

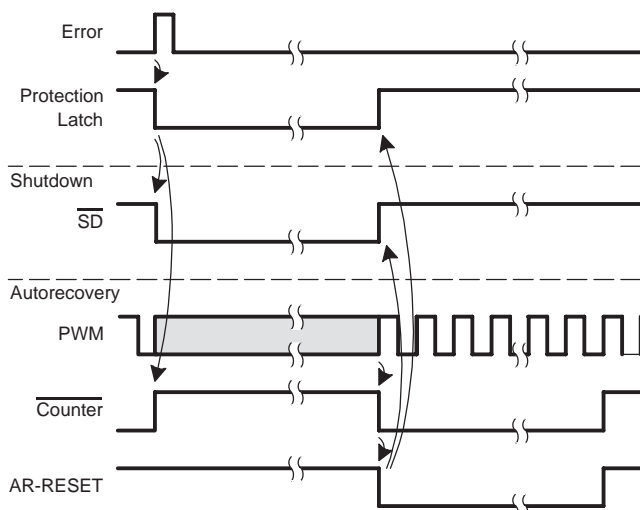


Figure 10. Autorecovery Function

Latching Shutdown on All Errors (PMODE1)

In latching shutdown mode, all error situations result in a power down (output stage Hi-Z). Re-enabling can be done by toggling the $\overline{\text{RESET}}$ pin.

All Protection Systems Disabled (PMODE2)

In PMODE2, all protection systems are disabled. This mode is purely intended for testing and characterization purposes and thus not recommended for normal device operation.

MODE Pins Selection

The protection mode is selected by shorting M1/M2 to DREG or DGND according to Table 2.

Table 2. Protection Mode Selection

| M1 | M2 | PROTECTION MODE |
|----|----|---|
| 0 | 0 | Autorecovery after errors (PMODE 0) |
| 0 | 1 | Latching shutdown on all errors (PMODE 1) |
| 1 | 0 | All protection systems disabled (PMODE 2) |
| 1 | 1 | Reserved |

The output configuration mode is selected by shorting the M3 pin to DREG or DGND according to Table 3.

Table 3. Output Mode Selection

| M3 | OUTPUT MODE |
|----|-------------------------------------|
| 0 | Bridge-tied load output stage (BTL) |
| 1 | Reserved |

APPLICATION INFORMATION

DEMODULATION FILTER DESIGN

The PurePath Digital amplifier outputs are driven by heavy-duty DMOS transistors in an H-bridge configuration. These transistors are either off or fully on, which reduces the DMOS transistor on-state resistance, $R(\text{DMOSon})$, and the power dissipated in the device, thereby increasing efficiency.

The result is a square-wave output signal with a duty cycle that is proportional to the amplitude of the audio signal. It is recommended that a second-order LC filter be used to recover the audio signal. For this application, EMI is considered important; therefore, the selected filter is the full-output type shown in Figure 11.

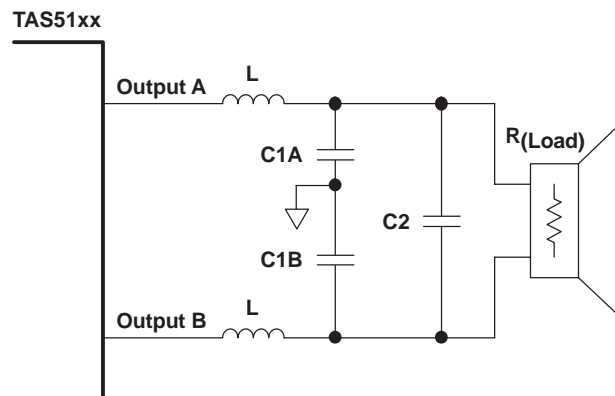


Figure 11. Demodulation Filter

The main purpose of the output filter is to attenuate the high-frequency switching component of the PurePath Digital amplifier while preserving the signals in the audio band.

Design of the demodulation filter affects the performance of the power amplifier significantly. As a result, to ensure proper operation of the overcurrent (OC) protection circuit and meet the device THD+N specifications, the selection of the inductors used in the output filter must be considered according to the following. The rule is that the inductance should remain stable within the range of peak current seen at maximum output power and deliver at least $5 \mu\text{H}$ of inductance at 15 A.

If this rule is observed, the TAS5112 does not have distortion issues due to the output inductors and overcurrent conditions do not occur due to inductor saturation in the output filter.

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Another parameter to be considered is the idle current loss in the inductor. This can be measured or specified as inductor dissipation (D). The target specification for dissipation is less than 0.05.

In general, 10- μ H inductors suffice for most applications. The frequency response of the amplifier is slightly altered by the change in output load resistance; however, unless tight control of frequency response is necessary (better than 0.5 dB), it is not necessary to deviate from 10 μ H.

The graphs in Figure 12 display the inductance vs current characteristics of two inductors that are recommended for use with the TAS5112.

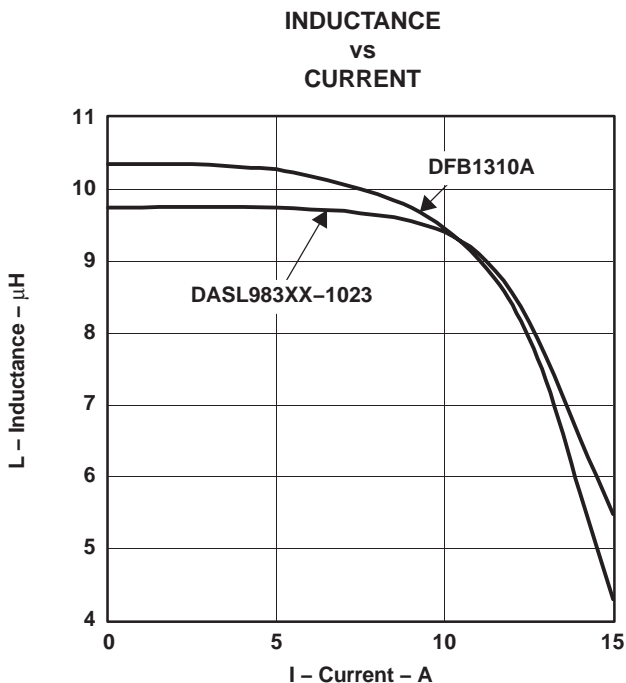


Figure 12. Inductance Saturation

The selection of the capacitor that is placed across the output of each inductor (C2 in Figure 11) is simple. To complete the output filter, use a 0.47- μ F capacitor with a voltage rating at least twice the voltage applied to the output stage (PVDD).

This capacitor should be a good quality polyester dielectric such as a Wima MKS2-047ufd/100/10 or equivalent.

In order to minimize the EMI effect of unbalanced ripple loss in the inductors, 0.1- μ F 50-V SMD capacitors (X7R or better) (C1A and C1B in Figure 11) should be added from the output of each inductor to ground.

THERMAL INFORMATION

The thermally augmented package provided with the TAS5112 is designed to be interfaced directly to heatsinks using a thermal interface compound (for example, Wakefield Engineering type 126 thermal grease.) The heatsink then absorbs heat from the ICs and couples it to the local air. If the heatsink is carefully designed, this process can reach equilibrium and heat can be continually removed from the ICs. Because of the efficiency of the TAS5112, heatsinks can be smaller than those required for linear amplifiers of equivalent performance.

$R_{\theta JA}$ is a system thermal resistance from junction to ambient air. As such, it is a system parameter with roughly the following components:

- $R_{\theta JC}$ (the thermal resistance from junction to case, or in this case the metal pad)
- Thermal grease thermal resistance
- Heatsink thermal resistance

$R_{\theta JC}$ has been provided in the *General Information* section.

The thermal grease thermal resistance can be calculated from the exposed pad area and the thermal grease manufacturer's area thermal resistance (expressed in $^{\circ}\text{C}\text{-in}^2/\text{W}$). The area thermal resistance of the example thermal grease with a 0.002-inch thick layer is about 0.1 $^{\circ}\text{C}\text{-in}^2/\text{W}$. The approximate exposed pad area is as follows:

56-pin HTSSOP 0.045 in²

Dividing the example thermal grease area resistance by the surface area gives the actual resistance through the thermal grease for both ICs inside the package:

56-pin HTSSOP 2.27 $^{\circ}\text{C}/\text{W}$

The thermal resistance of thermal pads is generally considerably higher than a thin thermal grease layer. Thermal tape has an even higher thermal resistance. Neither pads nor tape should be used with either of these two packages. A thin layer of thermal grease with careful clamping of the heatsink is recommended. It may be difficult to achieve a layer 0.001-inch thick or less, so the modeling below is done with a 0.002-inch thick layer, which may be more representative of production thermal grease thickness.

Heatsink thermal resistance is generally predicted by the heatsink vendor, modeled using a continuous flow dynamics (CFD) model, or measured.

Thus, for a single monaural IC, the system $R_{\theta JA} = R_{\theta JC} +$ thermal-grease resistance + heatsink resistance.

Table 4, Table 5, and Table 6 indicate modeled parameters for one or two TAS5112 ICs on a single heatsink. The final junction temperature is set at 110 $^{\circ}\text{C}$ in

all cases. It is assumed that the thermal grease is 0.002 inch thick and that it is similar in performance to Wakefield Type 126 thermal grease. It is important that the thermal grease layer is ≤ 0.002 inches thick and that thermal pads or tape are not used in the pad-to-heatsink interface due to the high power density that results in these extreme power cases.

Table 4. Case 1 (2 × 50 W Unclipped Into 6 Ω, Both Channels in Same IC) (1)

| | 56-Pin HTSSOP |
|--------------------------------------|--------------------------------------|
| Ambient temperature | 25°C |
| Power to load (per channel) | 50 W (unclipped) |
| Power dissipation | 4.5 W |
| Delta T inside package | 10.2°C, note 2 × channel dissipation |
| Delta T through thermal grease | 37.1°C, note 2 × channel dissipation |
| Required heatsink thermal resistance | 4.2°C/W |
| Junction temperature | 110°C |
| System R _{θJA} | 19°C/W |
| R _{θJA} * power dissipation | 85°C |
| Junction temperature | 85°C + 25°C = 110°C |

(1) This case represents a stereo system with only one package. See Case 2 and Case 2A if doing a full-power, 2-channel test in a multichannel system.

Table 5. Case 2 (2 × 50 W Unclipped Into 6 Ω, Channels in Separate Packages) (1)

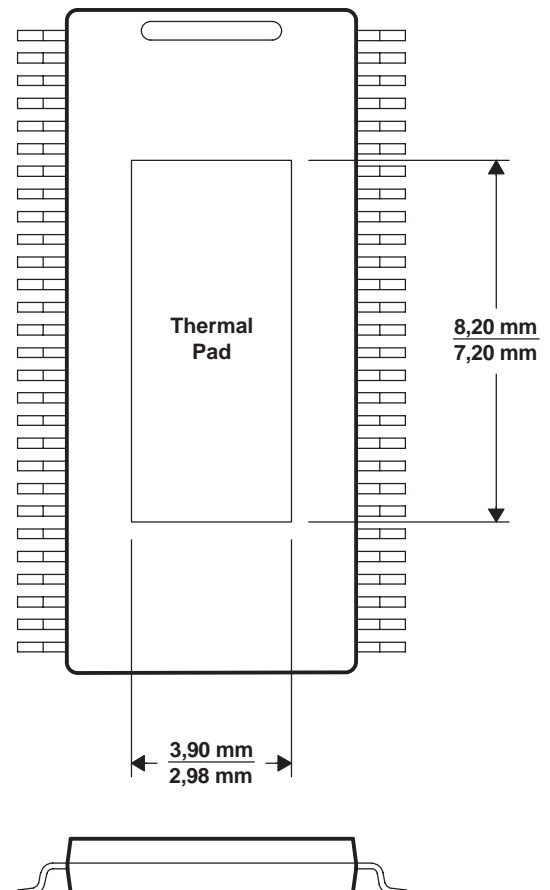
| | 56-Pin HTSSOP |
|--------------------------------------|---------------------|
| Ambient temperature | 25°C |
| Power to load (per channel) | 50 W (unclipped) |
| Power dissipation | 4.5 W |
| Delta T inside package | 5.1°C |
| Delta T through thermal grease | 18.6°C |
| Required heatsink thermal resistance | 6.9°C/W |
| Junction temperature | 110°C |
| System R _{θJA} | 19°C/W |
| R _{θJA} * power dissipation | 85°C |
| Junction temperature | 85°C + 25°C = 110°C |

(1) In this case, the power is separated into two packages. Note that this allows a considerably smaller heatsink because twice as much area is available for heat transfer through the thermal grease. For this reason, separating the stereo channels into two ICs is recommended in full-power stereo tests made on multichannel systems.

Table 6. Case 2A (2 × 60 W Unclipped Into 6 Ω, Channels in Separate IC Packages) (1)

| | 56-Pin HTSSOP |
|--------------------------------------|--------------------------------------|
| Ambient temperature | 25°C |
| Power to load (per channel) | 60 W (10% THD) |
| Power dissipation per channel | 5.4 W |
| Delta T inside package | 6.1°C, note 2 × channel dissipation |
| Delta T through thermal grease | 22.3°C, note 2 × channel dissipation |
| Required heatsink thermal resistance | 5.3°C/W |
| Junction temperature | 110°C |
| System R _{θJA} | 15.9°C/W |
| R _{θJA} * power dissipation | 85°C |
| Junction temperature | 85°C + 25°C = 110°C |

(1) In this case, the power is also separated into two packages, but overdriving causes clipping to 10% THD. In this case, the high power requires extreme care in attachment of the heatsink to ensure that the thermal grease layer is ≤ 0.002 inches thick. Note that this power level should not be attempted with both channels in a single IC because of the high power density through the thermal grease layer.



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CLICK AND POP REDUCTION

TI modulators feature a pop and click reduction system that controls the timing when switching starts and stops.

Going from nonswitching to switching operation causes a spectral energy burst to occur within the audio bandwidth, which is heard in the speaker as an audible click, for instance, after having asserted $\overline{\text{RESET}}$ LH during a system start-up.

To make this system work properly, the following design rules must be followed when using the TAS5112 back end:

- The relative timing between the PWM_AP/M_x signals and their corresponding VALID_x signal should not be skewed by inserting delays, because this increases the audible amplitude level of the click.
- The output stage must start switching from a fully discharged output filter capacitor. Because the output stage prior to operation is in the high-impedance state, this is done by having a passive pulldown resistor on each speaker output to GND (see *Typical System Configuration*).

Other things that can affect the audible click level:

- The spectrum of the click seems to follow the speaker impedance vs. frequency curve—the higher the impedance, the higher the click energy.
- Crossover filters used between woofer and tweeter in a speaker can have high impedance in the audio band, which should be avoided if possible.

Another way to look at it is that the speaker impulse response is a major contributor to how the click energy is shaped in the audio band and how audible the click will be.

The following mode transitions feature click and pop reduction.

| STATE | | CLICK AND POP REDUCED |
|-----------------------|---------------------------|-----------------------|
| Normal ⁽¹⁾ | → Mute | Yes |
| Mute | → Normal ⁽¹⁾ | Yes |
| Normal ⁽¹⁾ | → Error recovery (ERRCVY) | Yes |
| Error recovery | → Normal ⁽¹⁾ | Yes |
| Normal ⁽¹⁾ | → Hard Reset | No |
| Hard Reset | → Normal ⁽¹⁾ | Yes |

⁽¹⁾ Normal = switching

REFERENCES

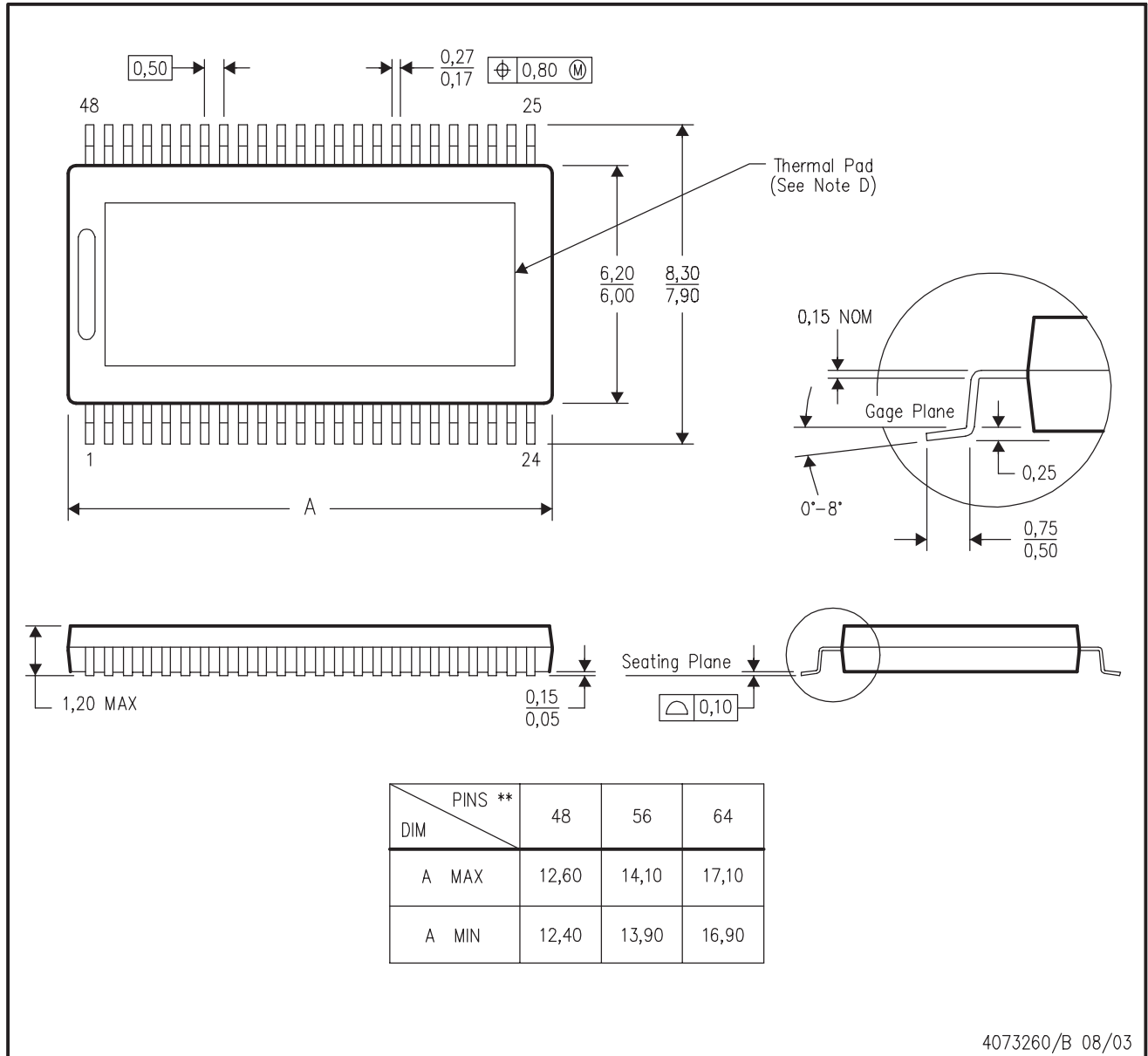
1. *TAS5000 Digital Audio PWM Processor* data manual—TI (SLAS270)
2. *True Digital Audio Amplifier TAS5001 Digital Audio PWM Processor* data sheet—TI (SLES009)
3. *True Digital Audio Amplifier TAS5010 Digital Audio PWM Processor* data sheet—TI (SLAS328)
4. *True Digital Audio Amplifier TAS5012 Digital Audio PWM Processor* data sheet—TI (SLES006)
5. *TAS5026 Six-Channel Digital Audio PWM Processor* data manual—TI (SLES041)
6. *TAS5036A Six-Channel Digital Audio PWM Processor* data manual—TI (SLES061)
7. *TAS3103 Digital Audio Processor With 3D Effects* data manual—TI (SLES038)
8. *Digital Audio Measurements* application report—TI (SLAA114)
9. *PowerPAD™ Thermally Enhanced Package* technical brief—TI (SLMA002)
10. *System Design Considerations for True Digital Audio Power Amplifiers* application report—TI (SLAA117)

MECHANICAL DATA

DFD (R-PDSO-G**)

PowerPAD™ PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)

48 PIN SHOWN



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions include mold flash or protrusion.
 - D. The package thermal performance may be enhanced by attaching an external heatsink to the thermal pad. This pad is electrically and thermally connected to the backside of the die and possibly selected leads.
 - E. Falls within JEDEC MO-153

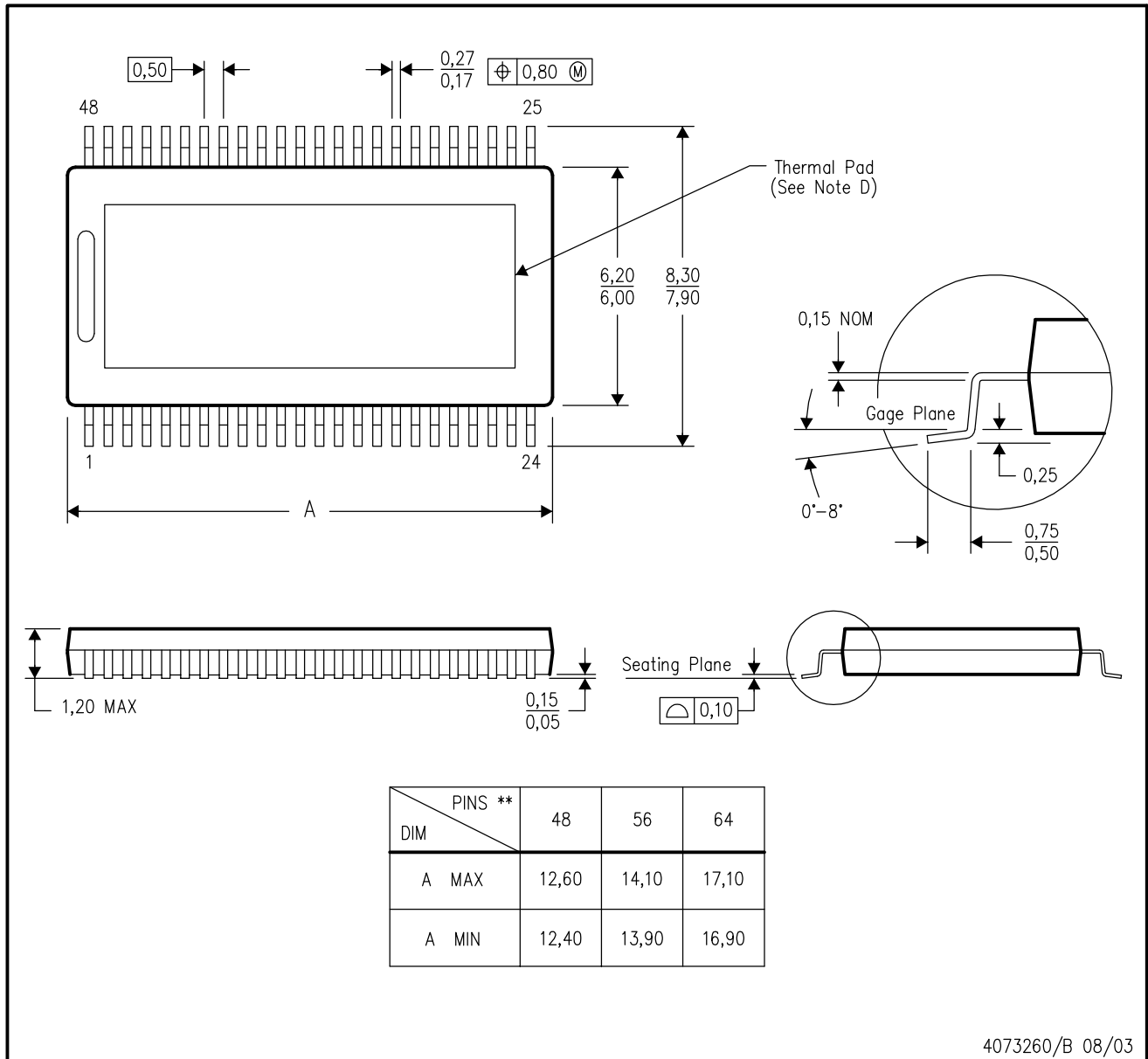
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